

Supporting Information

Probing Photovoltaic Performance in Copper Electrolyte Dye-Sensitized Solar Cells of Variable TiO₂ Particle Size Using Comprehensive Interfacial Analysis

Sourava Chandra Pradhan,^{ab} Jayadev Velore^{ab}, Anders Hagfeldt^{*c} and Suraj Soman^{*ab}

^aPhotosciences and Photonics Section, Chemical Sciences and Technology Division, CSIR-National Institute for Interdisciplinary Science and Technology (CSIR-NIIST), Thiruvananthapuram-695019, India. ^bAcademy of Scientific and Innovative Research (AcSIR), Ghaziabad-201002, India. ^cDepartment of Chemistry – Ångström Laboratory, Uppsala University Box 523, SE-75120 Uppsala, Sweden.

Email: suraj@niist.res.in

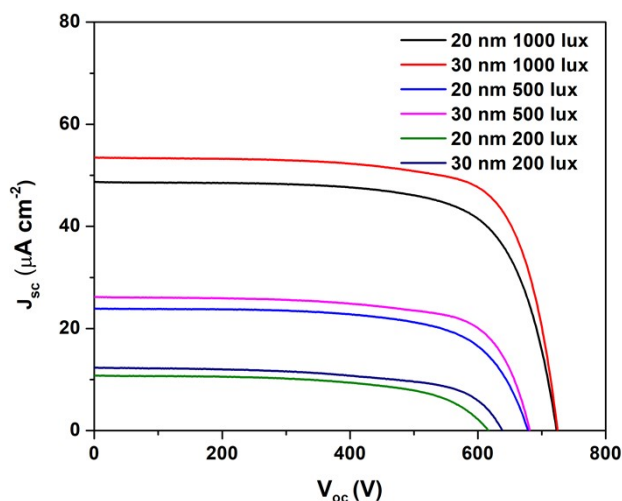


Figure S1. Current density - voltage (J - V) of DSCs fabricated with 20 nm and 30 nm TiO₂ particles employing D35 sensitizer and [Cu(tmby)₂]^{2+/1+} redox mediator under cfl light.

Table S1. Indoor photovoltaic parameter of DSCs fabricated with 20 nm and 30 nm TiO₂ particles employing D35 sensitizer and [Cu(tmby)₂]^{2+/1+} redox mediator under cfl light.

Device	Input power lux (μW/cm ²)	V _{oc} (mV)	J _{sc} (μA/cm ²):	FF	P _{max} (μW/cm ²)	PCE (%)
20 nm	1000 (283)	722 ± 1	48.68 ± 0.26	71.08 ± 0.33	25.01 ± 0.31	8.83 ± 0.11
	500 (143)	679 ± 4	23.92 ± 0.23	66.97 ± 0.37	10.88 ± 0.23	7.61 ± 0.16
	200 (59)	617 ± 2	10.79 ± 0.22	59.71 ± 0.25	3.98 ± 0.27	6.74 ± 0.14
30 nm	1000 (283)	727 ± 3	53.74 ± 0.22	75.14 ± 0.45	29.36 ± .74	10.37 ± 0.26
	500 (143)	687 ± 3	26.54 ± 0.20	73.95 ± 0.80	13.49 ± 0.20	9.43 ± 0.14
	200 (59)	639 ± 2	12.33 ± 0.10	61.43 ± 0.55	4.84 ± 0.33	8.21 ± 0.22

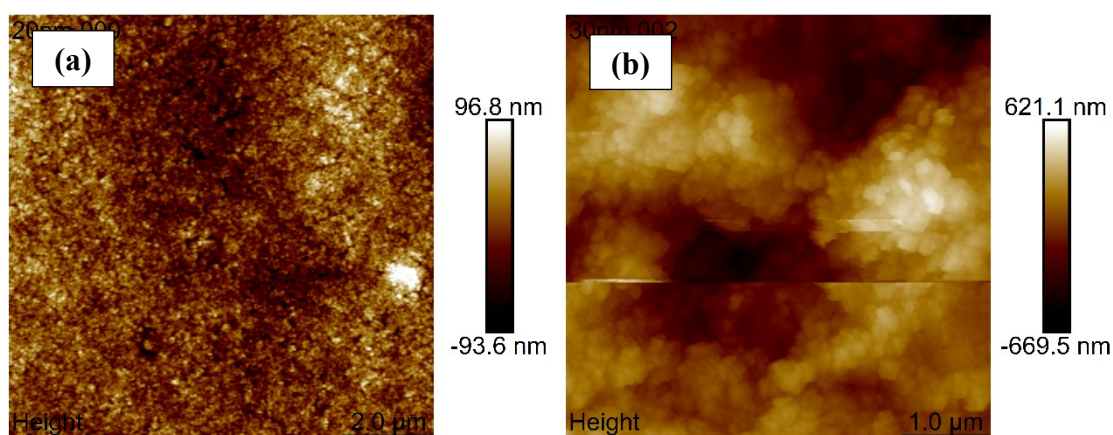


Figure S2. AMF image of TiO₂ film with (a) 20 nm (b) 30 nm diameter.

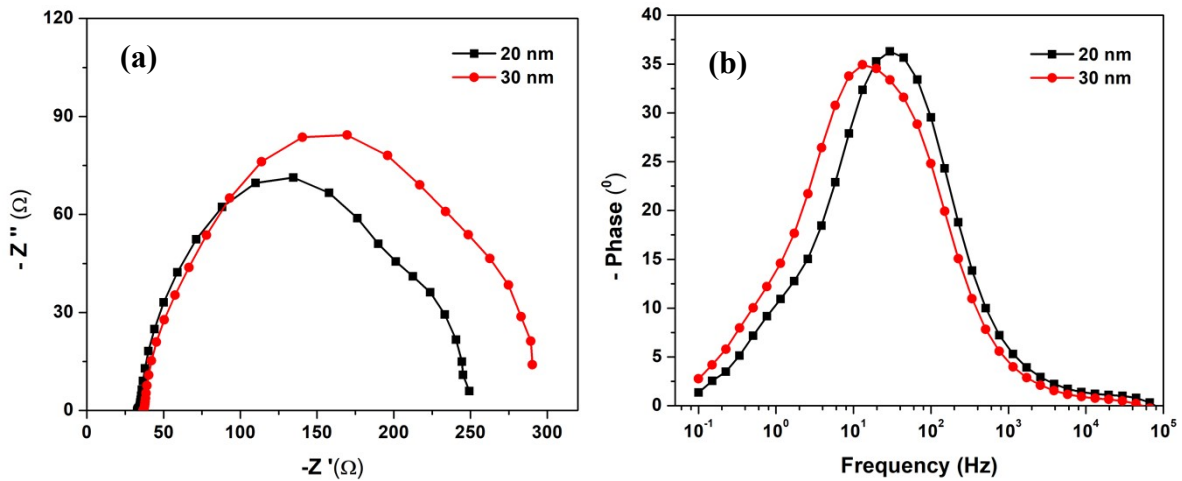


Figure S3. (a) Nyquist plot and **(b)** Bode plot of DSCs fabricated with 20 nm and 30 nm TiO₂ particles

EIS was measured at open circuit potential for both DSC with TiO₂ particle 20 nm and 30nm. Figure S2 (a) and (b) displays Nyquist plot and bode plot. The Nyquist plot consists of three distinguished semicircle, the semicircle at high frequency region corresponds to charge transfer at counter electrode electrolyte interface, second semicircle corresponds to charge transfer at TiO₂/electrolyte interface and the third semicircle corresponds to diffusion of ions on electrolyte. As seen in Figure S2 (a) the radius of second semicircle of 30 nm device is larger than 20 nm device which shows higher recombination resistance in 30 nm device than 20 nm device. We calculated lifetime (τ_n) from Bode plot using the relation, $\tau_n = 1/2\pi f_{max}$ where f_{max} is frequency at highest phase value. 30 nm device showed lifetime of 5.3 ms while 20 nm device showed 12.1 ms.

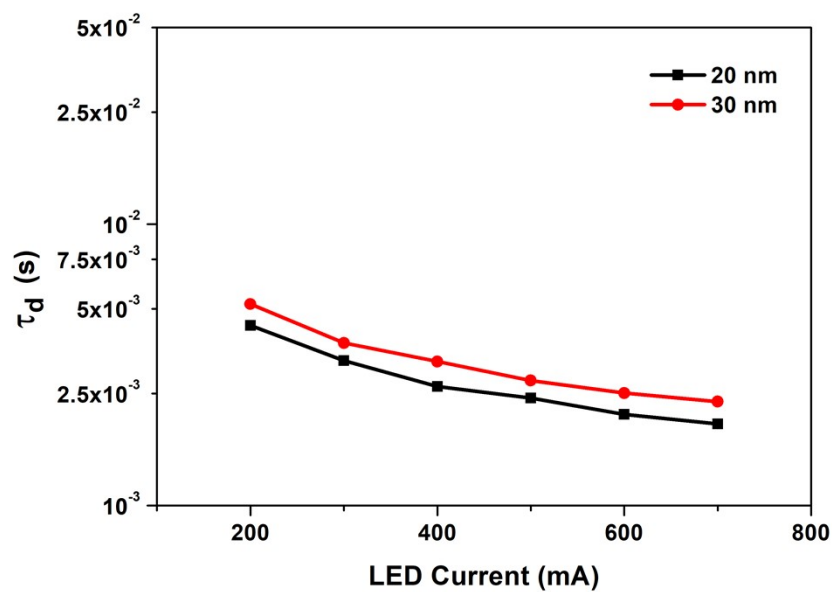


Figure S4. Transport time (τ_d) measurements using transient photocurrent decay for DSCs with 20 nm and 30 nm TiO_2 particles.